

Reg. No.

Question Paper Code

13696

B.E. / B.Tech. - DEGREE EXAMINATIONS, APRIL / MAY 2025

Second Semester

Electronics and Communication Engineering

(Common to Electrical and Electronics and Engineering & Computer and Communication Engineering)

20BSPH201 – PHYSICS OF ELECTRONIC DEVICES

Regulations - 2020

Duration: 3 Hours

Max. Marks: 100

PART - A (MCQ) (10 × 1 = 10 Marks)

Answer ALL Questions

- | | Marks | K – Level | CO |
|--|-------|-----------|-----|
| 1. The constant in Wiedemann–Franz law is called as:
(a) Avogadro constant (b) Planck constant
(c) Lorenz number (d) Boltzmann number | 1 | K1 | CO1 |
| 2. For free electrons in a three-dimensional metal, the density of states is proportional to
(a) E^0 (constant) (b) $E^{1/2}$ (c) E (d) $E^{3/2}$ | 1 | K2 | CO1 |
| 3. Which of the following dopants is usually used to construct an n-type extrinsic semiconductor?
(a) Boron (b) Phosphorus (c) Gallium (d) Indium | 1 | K1 | CO2 |
| 4. The physical process that is accountable for the coherent light emission in a laser diode?
(a) Spontaneous emission (b) Thermal radiation
(c) Stimulated emission (d) Impact ionization | 1 | K1 | CO2 |
| 5. The temperature above which ferromagnetic materials lose their magnetism is named:
(a) Curie temperature (b) Critical temperature
(c) Boiling point (d) Magnetic saturation temperature | 1 | K2 | CO3 |
| 6. Clausius-Mossotti equation is valid for:
(a) Highly conducting materials (b) Dense ionic solids only
(c) Homogeneous, isotropic, non-polar materials (d) Anisotropic magnetic materials | 1 | K2 | CO3 |
| 7. The relationship among emitter, base, and collector currents is:
$I_B = I_C - I_B$ (b) $I_C = I_E - I_B$ (c) $I_C = I_E - I_B$ (d) $I_E = I_B + I_C$ | 1 | K1 | CO4 |
| 8. The Hybrid- π model is predominantly used for:
(a) Small-signal analysis of BJTs (b) Large signal analysis of MOSFETs
(c) DC bias analysis of FETs (d) Power amplifier design | 1 | K1 | CO4 |
| 9. Compared to a JFET, a MOSFET has:
(a) Lower input impedance (b) Higher power dissipation
(c) Higher input impedance (d) Higher noise figure | 1 | K2 | CO5 |
| 10. A Light Emitting Diode (LED) emits light when:
(a) Reverse biased (b) Forward biased
(c) No voltage is applied (d) AC is applied | 1 | K1 | CO6 |

PART - B (12 × 2 = 24 Marks)

Answer ALL Questions

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|---|---|----|-----|
| 11. Define Fermi energy level. Give its significance. | 2 | K1 | CO1 |
| 12. State Electron effective mass. | 2 | K1 | CO1 |
| 13. Give two examples of an intrinsic semiconductor. | 2 | K1 | CO2 |
| 14. Draw the V-I characteristics of a PN junction diode in both forward and reverse bias. | 2 | K2 | CO2 |
| 15. Distinguish between Zener and avalanche breakdown. | 2 | K2 | CO2 |
| 16. On a microscopic level, how are magnetic materials classified? | 2 | K2 | CO3 |

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|--|---|----|-----|
| 17. Define saturation magnetization. | 2 | K1 | CO3 |
| 18. List the different types of polarization in dielectric materials. | 2 | K1 | CO3 |
| 19. Sketch the symbol of NPN and PNP transistor. | 2 | K2 | CO4 |
| 20. Mention the application where a multi-emitter transistor is normally used. | 2 | K1 | CO4 |
| 21. Define the threshold voltage of a MOSFET. | 2 | K1 | CO5 |
| 22. How does a CCD convert light into electronic signals? | 2 | K1 | CO5 |

PART - C (6 × 11 = 66 Marks)

Answer ALL Questions

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| 23. a) Obtain an expression for thermal conductivity in metals using classical theory. | 11 | K2 | CO1 |
| OR | | | |
| b) Derive the expression for the effective mass of an electron in a solid and explain its significance. | 11 | K2 | CO1 |
| 24. a) Deliberate the process of doping and how it alters the carrier concentration in semiconductors. | 11 | K3 | CO2 |
| OR | | | |
| b) Explain the working of a Zener diode and its characteristic breakdown behavior. | 11 | K3 | CO2 |
| 25. a) Describe domain theory in ferromagnetic materials. | 11 | K2 | CO3 |
| OR | | | |
| b) Explain the dielectric loss and derive an expression for it. | 11 | K2 | CO3 |
| 26. a) Explain the construction and working of a NPN transistor in CB configurations and discuss the input and output characteristics. | 11 | K3 | CO4 |
| OR | | | |
| b) Clarify how the Hybrid- π model simplifies the analysis of BJTs for amplifier design. | 11 | K3 | CO4 |
| 27. a) Elucidate the construction, working, and characteristics of D-MOSFET with a neat sketch. | 11 | K2 | CO5 |
| OR | | | |
| b) Illuminate the construction and working of a solar cell. Mention its merit and demerit. | 11 | K2 | CO5 |
| 28. a) Explain with a neat sketch the construction, working and characteristics of N-channel JFET. | 11 | K2 | CO6 |
| OR | | | |
| b) Explain the construction, working operation and characteristics of UJT with a neat sketch. | 11 | K2 | CO6 |